

BTA/BTB08 and T8 Series

8A TRIACs

SNUBBERLESS™, LOGIC LEVEL & STANDARD

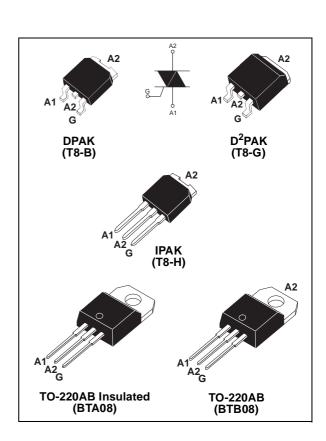
MAIN FEATURES:

Symbol	Value	Unit
I _{T(RMS)}	8	А
V _{DRM} /V _{RRM}	600 and 800	V
I _{GT (Q1)}	5 to 50	mA

DESCRIPTION

Available either in through-hole or surface-mount packages, the BTA/BTB08 and T8 triac series is suitable for general purpose AC switching. They can be used as an ON/OFF function in applications such as static relays, heating regulation, induction motor starting circuits... or for phase control operation in light dimmers, motor speed controllers,...

The snubberless versions (BTA/BTB...W and T8 series) are specially recommended for use on inductive loads, thanks to their high commutation performances. By using an internal ceramic pad, the BTA series provides voltage insulated tab (rated at 2500V RMS) complying with UL standards (File ref.: E81734)



ABSOLUTE MAXIMUM RATINGS

Symbol	Param	eter		Value	Unit
I _{T(RMS)}	RMS on-state current (full sine wave)	DPAK / D ² PAK IPAK / TO-220AB	Tc = 110°C	8	А
		TO-220AB Ins.	Tc = 100°C		
I _{TSM}	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	80	Α
	current (full cycle, Tj initial = 25°C)	F = 60 Hz	t = 16.7 ms	84	
l ² t	I ² t Value for fusing	tp = 10 r	ns	36	A ² s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, tr $\leq 100 \text{ ns}$	F = 120 Hz	Tj = 125°C	50	A/µs
I _{GM}	Peak gate current	tp = 20 μs	Tj = 125°C	4	Α
P _{G(AV)}	Average gate power dissipation		Tj = 125°C	1	W
T _{stg} T _j	Storage junction temperature range Operating junction temperature range	0,			

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BTA/BTB08 and T8 Series

ELECTRICAL CHARACTERISTICS (Tj = 25°C, unless otherwise specified)

■ SNUBBERLESS™ and LOGIC LEVEL (3 Quadrants)

Symbol	Test Conditions	Quadrant		Т	8	BTA/BTB08				Unit
			•	T810	T835	TW	SW	CW	BW	
I _{GT} (1)	$V_D = 12 \text{ V}$ $R_1 = 30 \Omega$	1 - 11 - 111	MAX.	10	35	5	10	35	50	mA
V _{GT}	VD = 12 V	1 - 11 - 111	MAX.			1	.3			V
V _{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ I - II - III Tj = 125°C		MIN.			0	.2			V
I _H (2)	I _T = 100 mA		MAX.	15	35	10	15	35	50	mA
IL	I _G = 1.2 I _{GT}	I - III	MAX.	25	50	10	25	50	70	mA
		II		30	60	15	30	60	80	
dV/dt (2)	$V_D = 67 \text{ %V}_{DRM}$ gate open Tj = 125°C		MIN.	40	400	20	40	400	1000	V/µs
(dl/dt)c (2)	(dV/dt)c = 0.1 V/µs Tj = 125°C		MIN.	5.4	-	3.5	5.4	-	-	A/ms
	$(dV/dt)c = 10 V/\mu s$ Tj = 125°C			2.8	-	1.5	2.8	-	-	
	Without snubber Tj = 1	25°C		-	4.5	-	-	4.5	7	

■ STANDARD (4 Quadrants)

Symbol	Test Conditions	Quadrant		BTA/E	BTB08	Unit
				С	В	Oilit
I _{GT} (1)	$V_D = 12 \text{ V}$ $R_L = 30 \Omega$	I - II - III IV	MAX.	25 50	50 100	mA
V _{GT}		ALL	MAX.	1.	.3	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $Tj = 125^{\circ}\text{C}$	ALL	MIN.	0.	.2	V
I _H (2)	I _T = 500 mA		MAX.	25	50	mA
Ι <u>L</u>	I _G = 1.2 I _{GT}	I - III - IV	MAX.	40	50	mA
		II		80	100	
dV/dt (2)	$V_D = 67 \text{ %}V_{DRM}$ gate open Tj = 125°C		MIN.	200	400	V/µs
dV/dt)c (2)	(dI/dt)c = 3.5 A/ms Tj = 125°C		MIN.	5	10	V/µs

STATIC CHARACTERISTICS

Symbol	Test Con	Test Conditions						
V _{TM} (2)	I _{TM} = 11 A tp = 380 μs	Tj = 25°C	MAX.	1.55	V			
V _{to} (2)	Threshold voltage Tj = 125°C MAX.		MAX.	0.85	V			
R _d (2)	Dynamic resistance $Tj = 125^{\circ}C$ MAX.		MAX.	50	mΩ			
I _{DRM}	$V_{DRM} = V_{RRM}$	Tj = 25°C	MAX.	5	μΑ			
I _{RRM}		Tj = 125°C	IVIAA.	1	mA			

Note 1: minimum IGT is guaranted at 5% of IGT max.

Note 2: for both polarities of A2 referenced to A1

THERMAL RESISTANCES

Symbol	Para	Parameter				
R _{th(j-c)}	Junction to case (AC)	tion to case (AC)		1.6	°C/W	
			TO-220AB Insulated	2.5	1	
R _{th(j-a)}	Junction to ambient	$S = 1 \text{ cm}^2$	D ² PAK	45	°C/W	
		$S = 0.5 \text{ cm}^2$	DPAK	70		
			TO-220AB TO-220AB Insulated	60		
			IPAK	100		

S = Copper surface under tab

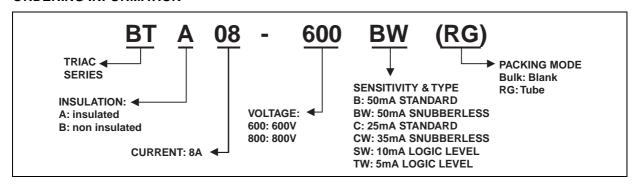
PRODUCT SELECTOR

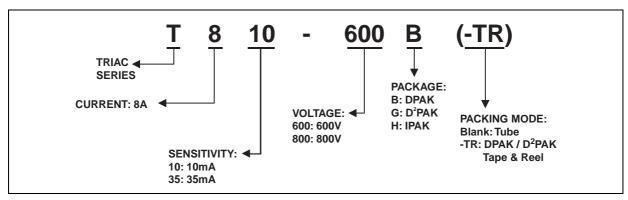
Part Number	Voltag	e (xxx)	Sensitivity	Туре	Package
T dit Humbon	600 V	800 V	_ comonava,	.,,,,,	. uougo
BTA/BTB08-xxxB	Х	Х	50 mA	Standard	TO-220AB
BTA/BTB108-xxxBW	Х	Х	50 mA	Snubberless	TO-220AB
BTA/BTB08-xxxC	Х	Х	25 mA	Standard	TO-220AB
BTA/BTB08-xxxCW	Х	Х	35 mA	Snubberless	TO-220AB
BTA/BTB08-xxxSW	Х	Х	10 mA	Logic level	TO-220AB
BTA/BTB08-xxxTW	Х	Х	5 mA	Logic level	TO-220AB
T810-xxxB	Х	Х	10 mA	Logic level	DPAK
T810-xxxH	Х	Х	10 mA	Logic level	IPAK
T835-xxxB	Х	Х	35mA	Snubberless	DPAK
T835-xxxG	Х	Х	35 mA	Snubberless	D²PAK
T835-xxxH	Х	Х	35 mA	Snubberless	IPAK

BTB: non insulated TO-220AB package

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ORDERING INFORMATION





OTHER INFORMATION

Part Number	Marking	Weight	Base quantity	Packing mode
BTA/BTB08-xxxyz	BTA/BTB08xxxyz	2.3 g	250	Bulk
BTA/BTB08-xxxyzRG	BTA/BTB08-xxxyz	2.3 g	50	Tube
T8yy-xxxB	Т8ууххх	0.3 g	75	Tube
T8yy-xxxB-TR	Т8ууххх	0.3 g	2500	Tape & reel
T8yy-xxxH	Т8ууххх	0.4 g	75	Tube
T8yy-xxxG	Т8ууххх	1.5 g	50	Tube
T8yy-xxxG-TR	Т8ууххх	1.5 g	1000	Tape & reel

Note: xxx = voltage, yy = sensitivity, z = type

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).

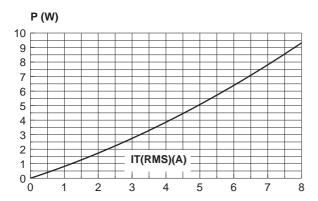


Fig. 2-2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35µm),full cycle.

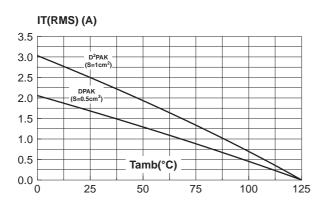


Fig. 4: On-state characteristics (maximum values).

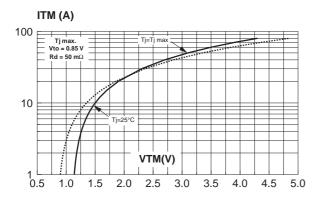


Fig. 2-1: RMS on-state current versus case temperature (full cycle).

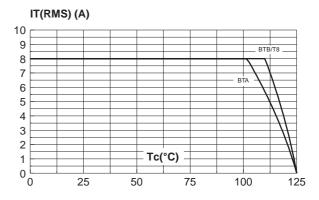


Fig. 3: Relative variation of thermal impedance versus pulse duration.

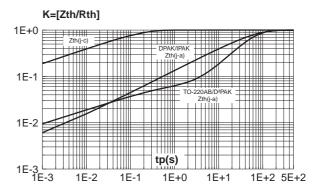
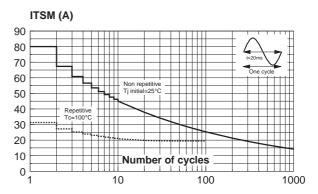


Fig. 5: Surge peak on-state current versus number of cycles.



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Fig. 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms, and corresponding value of I²t.

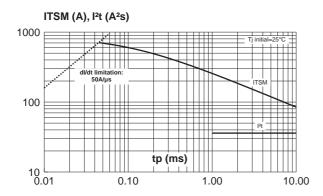


Fig. 8-1: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values). Snubberless & Logic Level Types

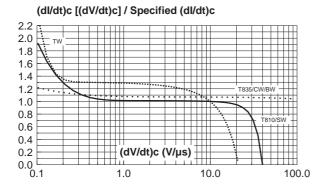


Fig. 9: Relative variation of critical rate of decrease of main current versus junction temperature.

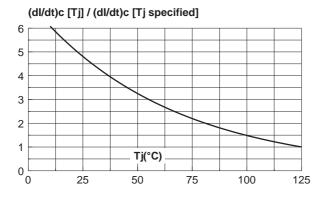


Fig. 7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

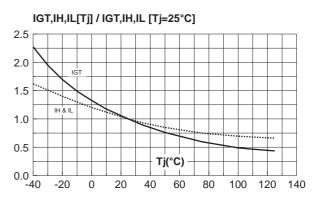


Fig. 8-2: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values). Standard Types

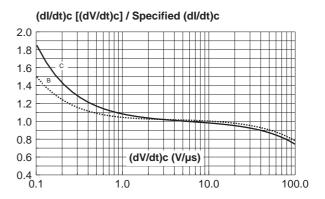
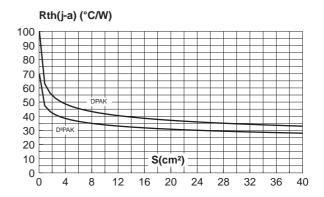
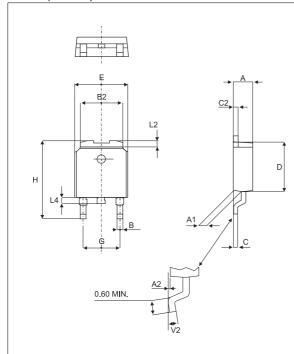


Fig. 10: DPAK and D^2PAK Thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: $35 \mu m$).



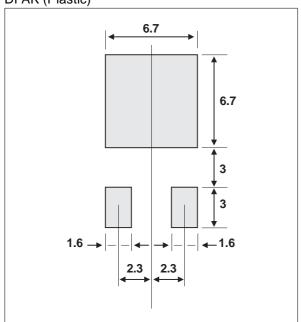
DPAK (Plastic)



		DIMEN	ISIONS	
REF.	Millim	neters	Inc	hes
	Min.	Max	Min.	Max.
Α	2.20	2.40	0.086	0.094
A1	0.90	1.10	0.035	0.043
A2	0.03	0.23	0.001	0.009
В	0.64	0.90	0.025	0.035
B2	5.20	5.40	0.204	0.212
С	0.45	0.60	0.017	0.023
C2	0.48	0.60	0.018	0.023
D	6.00	6.20	0.236	0.244
Е	6.40	6.60	0.251	0.259
G	4.40	4.60	0.173	0.181
Н	9.35	10.10	0.368	0.397
L2	0.80	typ.	0.03	1 typ.
L4	0.60	1.00	0.023	0.039
R	0.2	typ.	0.00	7 typ.
V2	0°	8°	0°	8°

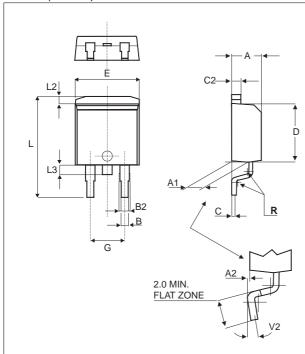
FOOTPRINT DIMENSIONS (in millimeters)

DPAK (Plastic)



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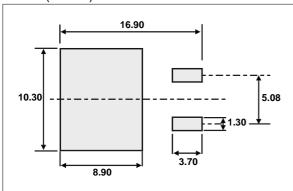
D²PAK (Plastic)



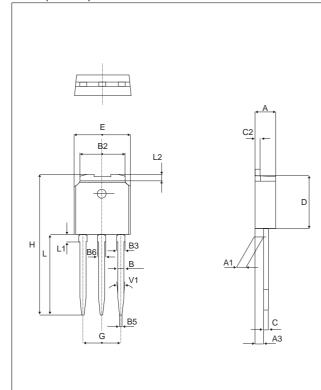
			DIMEN	SIONS		
REF.	М	illimete	rs		Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.70		0.93	0.027		0.037
B2	1.25	1.40		0.048	0.055	
С	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	8.95		9.35	0.352		0.368
E	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.40	0.050		0.055
L3	1.40		1.75	0.055		0.069
R		0.40			0.016	
V2	0°		8°	0°		8°

FOOTPRINT DIMENSIONS (in millimeters)

D²PAK (Plastic)

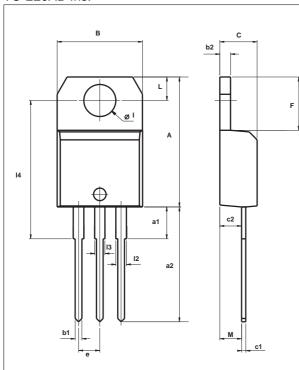


IPAK (Plastic)



			DIMEN	ISIONS		
REF.	М	illimete	rs	Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
А3	0.7		1.3	0.027		0.051
В	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
В3			0.85			0.033
B5		0.3			0.035	
B6			0.95			0.037
С	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
Е	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
Н	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039
V1		10°			10°	

TO-220AB Ins.



			DIMEN	SIONS		
REF.	М	illimete	rs		Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
В	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
С	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
е	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
1	3.75		3.85	0.147		0.151
14	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
12	1.14		1.70	0.044		0.066
13	1.14		1.70	0.044		0.066
М		2.60			0.102	

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